

**Appln No. 10/712,364**  
**Amdt date October 13, 2005**  
**Reply to Office action of August 18, 2005**

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. - 15. (Canceled)
16. (New) A semiconductor wafer machining method for machining a semiconductor wafer, comprising the steps of:  
    carrying out an entire cut through the semiconductor wafer with a cutting blade to form lateral surfaces; and  
    irradiating the lateral surfaces of the cut with laser light to form a modified layer by melting.
17. (New) The semiconductor wafer machining method according to claim 16, wherein an entirety of the lateral surfaces of the semiconductor wafer is irradiated with the laser light.
18. (New) The semiconductor wafer machining method according to claim 16, wherein the laser is a YAG laser or a CO<sub>2</sub> laser.
19. (New) The semiconductor wafer machining method according to claim 16, wherein a dicing tape is adhered to a surface of the semiconductor wafer; and the laser light is irradiated after cutting only the semiconductor wafer and expanding the dicing tape.
20. (New) The semiconductor wafer machining method according to claim 16, wherein the laser light is irradiated onto the lateral surface of a first cut that has been already formed and is different from a second cut being formed by the cutting blade.

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21. (New) The semiconductor wafer machining method according to claim 16, wherein the laser light is irradiated onto the lateral surfaces of the cut that is being formed by cutting the semiconductor wafer by the cutting blade while following the movement of the cutting blade.